NSN 5961-01-307-7191

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-307-7191 **Inclosure Material:** Metal **Overall Length:** 0.180 inches **Terminal Length:** 1.015 inches **Overall Diameter:** 0.366 inches **Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method: Terminal Terminal Circle Diameter:** 0.210 inches **Features Provided:** Hermetically sealed case and electrostatic sensitive **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 700.0 nonrepetitive peak reverse voltage and 700.0 nonrepetitive peak off-state voltage and 600.0 repetitive peak off-state voltage **Current Rating Per Characteristic:** 100.00 amperes peak forward surge current absolute **Power Rating Per Characteristic:** 40.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius case **Special Features:** Junction pattern arrangement: pnpn **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: